

Features

- Current transfer ratio (CTR: 20~300% at $I_F = \pm 10\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso =5000Vrms)
- Collector - emitter breakdown voltage $V_{CE0} \geq 80\text{V}$
- Operating Temperature: -55 ~110
- Environmentally friendly products, compliant with CQC, UL, and VDE requirements

Mechanical Data

- Case: DIP4 DIP4 - M SMD4
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals:



XL814

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Input	Forward Current	I _F	±60	mA
	Power Dissipation	PD	100	mW
	Power Dissipation Derating factor (above T _a = 100°C)	PDD	2.9	mW/°C
	Thermal Resistance Junction-Ambient	R _{thJ-A}	325	°C/W
	Thermal Resistance Junction-Case	R _{thJ-C}	200	°C/W
Output	Power Dissipation	PC	150	mW
	Collector Current	I _C	50	mA
	Collector-Emitter Voltage	V _{CEO}	80	V
	Emitter-Collector Voltage	V _{ECO}	7	V

Thermal Characteristics

Parameter	Symbol	Value	Unit
Total Power Dissipation	PTOT	200	mW
Isolation Voltage *1	VISO	5000	V _{rms}
Operating Temperature	TOPR	-55 ~ +100	°C
Storage Temperature Range	TSTG	-55 ~ +125	°C
Soldering Temperature *2	TSOL	260	°C

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Electrical Characteristics (@ T_a = 25°C unless otherwise specified)

	Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V _F	I _F = ±20mA	-	1.2	1.4	V
	Terminal Capacitance	C _t	V = 0, f = 1kHz	-	30	250	pF
	Collector-Emitter Dark Current	I _{CEO}	V _{CE} = 20V, I _F = 0	-	-	100	nA
Output	Collector-Emitter Breakdown Voltage	V _{BR}					



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